ABSTRACT

A measurement method includes a preparation step of electrically connecting a first wiring and a second wiring to a semiconductor device, and a measurement step of measuring, by a measurement instrument, a measurement value corresponding to a current flowing through the first wiring and the second wiring while irradiating the semiconductor device with a light beam, in order to observe an electrical response of the semiconductor device caused by irradiating the semiconductor device with the light beam. In the preparation step, the first wiring and the second wiring are arranged such that the first wiring and the second wiring form at least a first loop portion and a second loop portion in which directions of current flow are opposite to each other when viewed from a predetermined direction. In the measurement step, the measurement value is measured in a state in which the first loop portion and the second loop portion are formed.

Fig. 2